



#### **NCE N-Channel Super Trench II Power MOSFET**

#### **Description**

The series of devices uses **Super Trench II** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{\text{DS(ON)}}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification.

#### **Application**

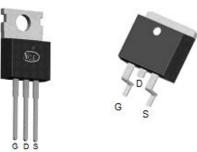
- DC/DC Converter
- •Ideal for high-frequency switching and synchronous rectification

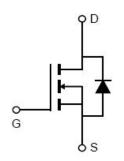
#### **General Features**

- $V_{DS}$  =200V, $I_D$  =125A  $R_{DS(ON)}$ =7.7m $\Omega$  , typical (TO-220)@  $V_{GS}$ =10V  $R_{DS(ON)}$ =7.5m $\Omega$  , typical (TO-263)@  $V_{GS}$ =10V
- Excellent gate charge x R<sub>DS(on)</sub> product(FOM)
- Very low on-resistance R<sub>DS(on)</sub>
- 175 °C operating temperature
- Pb-free lead plating

100% UIS TESTED! 100% ΔVds TESTED!







Schematic Diagram

#### **Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP090N20	NCEP090N20	TO-220-3L	-	-	-
NCEP090N20D	NCEP090N20D	TO-263-2L	-	-	-

Absolute Maximum Ratings (T<sub>c</sub>=25 ℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	200	V
Gate-Source Voltage	V <sub>G</sub> s	±20	V
Drain Current-Continuous	I <sub>D</sub>	125	Α
Drain Current-Continuous(T <sub>C</sub> =100 °C)	I <sub>D</sub> (100℃)	88	А
Pulsed Drain Current	I <sub>DM</sub>	500	А
Maximum Power Dissipation	P <sub>D</sub>	340	W
Derating factor		2.27	W/°C
Single pulse avalanche energy (Note 1)	E <sub>AS</sub>	1692	mJ
Operating Junction and Storage Temperature Range	$T_{J}, T_{STG}$	-55 To 175	$^{\circ}$

#### **Thermal Characteristic**

Thermal Resistance,Junction-to-Case	Rejc	0.44	°C/W



### Electrical Characteristics (T<sub>C</sub>=25°C unless otherwise noted)

Parameter	Symbol	Condition		Min	Тур	Max	Unit
Off Characteristics				•			
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA		200	-	-	V
Zero Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =200V,V <sub>GS</sub> =0V		-	-	1	μΑ
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V		-	-	±100	nA
On Characteristics	·						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =250μA		2.0	3.0	4.0	V
Dunin Course On State Besistance	В	V <sub>GS</sub> =10V, I <sub>D</sub> =20A	TO-220	-	7.7	9.0	mΩ
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>		TO-263	-	7.5	9.0	
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =10V,I <sub>D</sub>	=20A	70	-	-	S
Dynamic Characteristics	·			•			
Input Capacitance	C <sub>lss</sub>	- V <sub>DS</sub> =100V,V <sub>GS</sub> =0V, - F=1.0MHz		-	6000	-	PF
Output Capacitance	Coss			-	535	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>			-	17.5	-	PF
Switching Characteristics (Note 2)				•			
Turn-on Delay Time	t <sub>d(on)</sub>	$V_{DD}$ =100V, $I_{D}$ =20A $V_{GS}$ =10V, $R_{G}$ =4.7 $\Omega$		-	54	-	nS
Turn-on Rise Time	tr			-	38	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>			-	65	-	nS
Turn-Off Fall Time	t <sub>f</sub>			-	15	-	nS
Total Gate Charge	Qg	V <sub>DS</sub> =100V,I <sub>D</sub> =20A, V <sub>GS</sub> =10V		-	95		nC
Gate-Source Charge	Q <sub>gs</sub>			-	30.5		nC
Gate-Drain Charge	Q <sub>gd</sub>			-	24.5		nC
Drain-Source Diode Characteristics				•			•
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub>	=20A	-		1.2	V
Diode Forward Current	Is			-	-	125	Α
Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> = 25°C, I <sub>F</sub> = 50A		-	98		nS
Reverse Recovery Charge	Qrr	di/dt = 100A/μs		-	260		nC

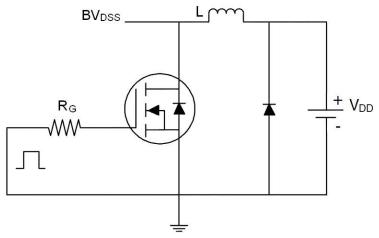
#### Notes:

- 1. EAS condition : Tj=25  $^{\circ}\text{C}$  ,VDD=50V,VG=10V,L=0.5mH,Rg=25 $\Omega$
- 2. Guaranteed by design, not subject to production
- 3. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heat sink, assuming a maximum junction temperature of TJ(MAX)=175° C. The SOA curve provides a single pulse rating.

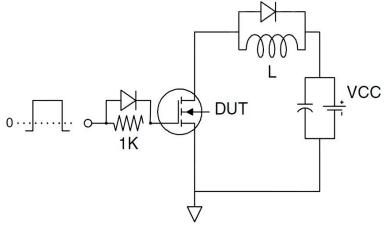


#### **Test Circuit**

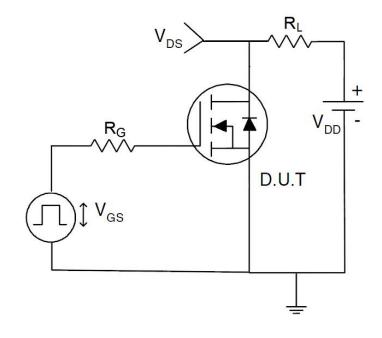
#### 1) E<sub>AS</sub> test Circuit



#### 2) Gate charge test Circuit

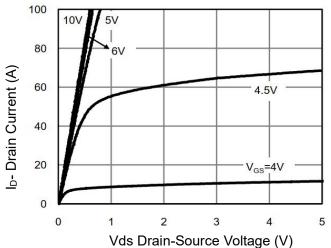


#### 3) Switch Time Test Circuit

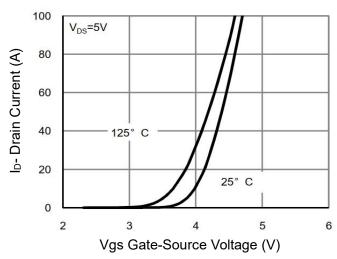




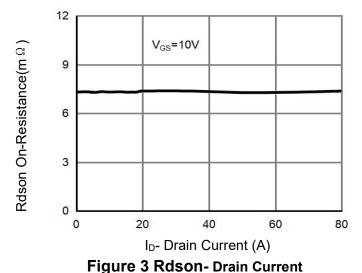
#### **Typical Electrical and Thermal Characteristics**



**Figure 1 Output Characteristics** 



**Figure 2 Transfer Characteristics** 



2.6 2.4 Normalized On-Resistance 2.2 V<sub>GS</sub>=10V I<sub>D</sub>=20A 2 1.8 1.6 1.4 1.2 0.8 50 75 100 125 150 175 T<sub>J</sub>-Junction Temperature(°C)

Figure 4 Rdson-JunctionTemperature

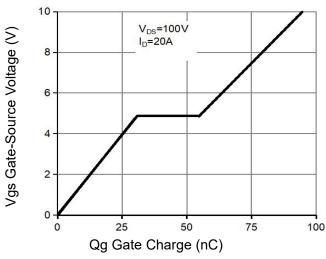


Figure 5 Gate Charge

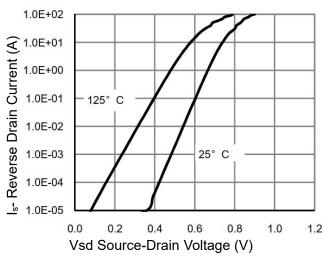


Figure 6 Source- Drain Diode Forward





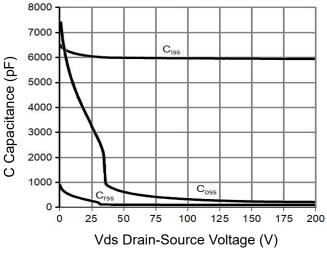


Figure 7 Capacitance vs Vds

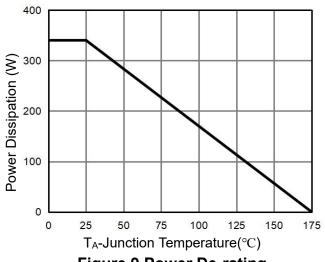


Figure 9 Power De-rating

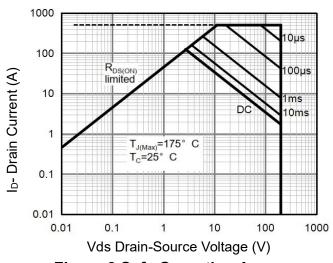


Figure 8 Safe Operation Area (Note3)

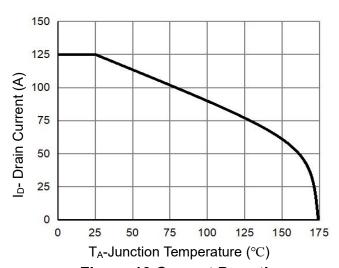
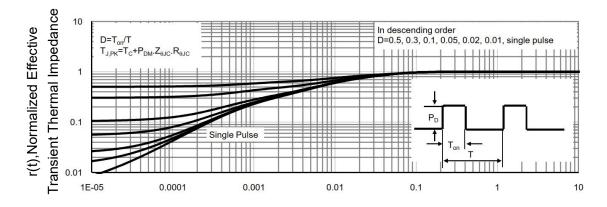


Figure 10 Current De-ratin



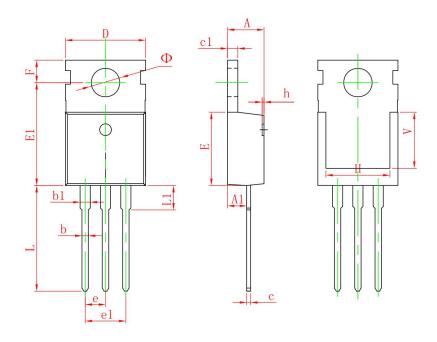
Square Wave Pluse Duration(sec)

**Figure 11 Normalized Maximum Transient Thermal Impedance** 

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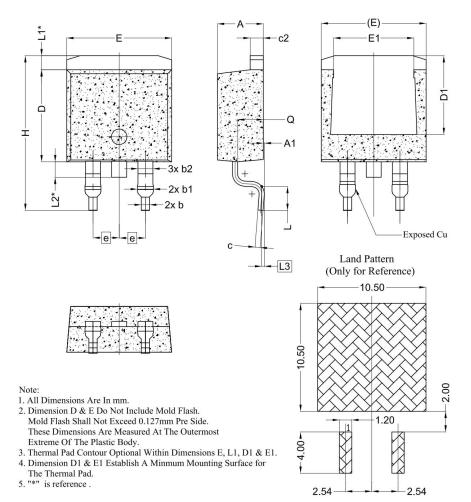
### **TO-220-3L Package Information**



Cumbal	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
Α	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
E	8.950	9.750	0.352	0.384	
E1	12.650	13.050	0.498	0.514	
е	2.540	TYP.	0.100 TYP.		
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	6.900	REF.	0.276 REF.		
Φ	3.400	3.800	0.134	0.150	



#### **TO-263-2L Package Information**



SYMBOL	DIMENSIONS				
STIMBUL	MIN. NOM.		MAX.		
А	4.24	4.44	4.64		
A1	0.00	0.10	0.25		
b	0.70	0.80	0.90		
b1	1.20	1.55	1.75		
b2	1.20 1.45		1.70		
С	0.40 0.50		0.60		
c2	1.15	1.27	1.40		
D	8.82	8.92	9.02		
D1	6.86 7.65		_		
Е	9.96 10.16		10.36		
E1	6.89 7.77		7.89		
е	2.54 BSC				
Н	14.61 15.00		15.88		
L	1.78	2.32	2.79		
L1	1.36 REF.				
L2	1.50 REF.				
L3	0.25 BSC				
Q	2.30 2.48 2.70				



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